AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A light-emitting device comprising:

a semiconductor light-emitting element comprising:

a substrate surface, a surface of which being ~~as~~ a main light-extracting surface;

a light-emitting layer formed on said substrate; and

a reflective p-type electrode formed on said light-emitting layer; and

a mount frame on which said semiconductor light-emitting element is mounted and which comprises a reflecting portion for reflecting light emitted from said substrate surface,

wherein said mount frame comprises a swollen portion formed within said reflecting portion such that a part of said substrate surface is supported by said swollen portion to thereby mount said light-emitting element on said mount frame, said swollen portion comprising a substantially flat top surface to support said substrate surface.

2. (Original) A light-emitting device according to claim 1, wherein said swollen portion is formed so as to be integrated with said mount frame.

3. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion comprises a rotationally symmetric member protruded from nearly the center of a bottom surface of said reflecting portion of said mount frame.

4. (Previously Presented) A light-emitting device according to claim 3, wherein said swollen portion comprises an inclined surface.

5. (Original) A light-emitting device according to claim 1, wherein said swollen portion supports substantially the position of the center of gravity of said substrate surface.

6. (Currently Amended) A light-emitting device according to claim 1, wherein said swollen portion supports substantially the position of the center of gravity of [[a]] said p-type electrode of ~~in~~ said light-emitting element.

7. (Original) A light-emitting device according to claim 1, wherein said swollen portion supports a surface below an n electrode in said light-emitting element.

8. (Currently Amended) A light-emitting device according to claim 1, wherein a plurality of bonding wires are connected to [[a]] said p-type electrode of ~~in~~ said light-emitting element.

9. (Original) A light-emitting device according to claim 1, where said semiconductor light-emitting element comprises a Group III nitride compound semiconductor light-emitting element.

10. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion comprises substantially cross-shaped reinforcing walls.

11. (Currently Amended) A light-emitting device according to claim 1, further comprising:

an n electrode formed in a center portion of the light-emitting ~~element; and~~ element, wherein said p-type ~~a p~~ electrode is formed annularly ~~formed~~ around the n electrode.

12. (Previously Presented) A light-emitting device according to claim 1, wherein light released from said substrate is reflected uniformly in all directions by a side surface of said swollen portion.

13. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion is integrally formed with said mount frame.

14. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion comprises a same material as said mount frame.

15. (Canceled)

16. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion is formed separately from said mount frame.

17. (Previously Presented) A light-emitting device according to claim 16, wherein said swollen portion comprises a metal material having a high thermal conductivity.

18. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion comprises a rotationally symmetric member disposed substantially at a center of said reflecting portion.

19. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion comprises an inclined surface.

20. (Canceled)

21. (Previously Presented) A light-emitting device according to claim 11, wherein said swollen portion is disposed below said n electrode.

22. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion contacts said substrate surface.

23. (Previously Presented) A light-emitting device according to claim 1, wherein said swollen portion has a shape of a truncated cone.

24. (Previously Presented) A light-emitting device according to claim 1, wherein less than an entirety of said substrate surface is supported by said swollen portion.

25. (Previously Presented) A light-emitting device according to claim 1, wherein light is released exclusively from said substrate surface.

26. (Previously Presented) A light-emitting device according to claim 1, wherein a height of said mount frame is substantially equal to a height of said swollen portion.

27. (Previously Presented) A light-emitting device according to claim 1, wherein said semiconductor light-emitting element comprises an electrode which reflects light in a direction of said swollen portion.

28. (New) A light-emitting device according to claim 1, wherein said p-type electrode comprises a metal selected from the group consisting of Rh, Pt, Ru or an alloy of said metal.

29. (New) A light-emitting device according to claim 1, wherein said light-emitting element comprises a flip-chip type light-emitting element.